



**THE DATASHEET OF  
PBSS303NX,115**



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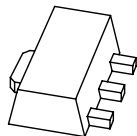
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Kind regards,

Team Nexperia



# PBSS303NX

30 V, 5.1 A NPN low  $V_{CEsat}$  (BISS) transistor

Rev. 02 — 20 November 2009

Product data sheet

## 1. Product profile

### 1.1 General description

NPN low  $V_{CEsat}$  Breakthrough In Small Signal (BISS) transistor in a SOT89 (SC-62/TO-243) small and flat lead Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS303PX.

### 1.2 Features

- Low collector-emitter saturation voltage  $V_{CEsat}$
- High collector current capability  $I_C$  and  $I_{CM}$
- High collector current gain ( $h_{FE}$ ) at high  $I_C$
- High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

### 1.3 Applications

- DC-to-DC conversion
- MOSFET gate driving
- Motor control
- Charging circuits
- Power switches (e.g. motors, fans)

### 1.4 Quick reference data

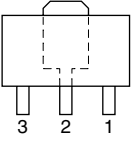
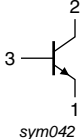
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	30	V
$I_C$	collector current		-	-	5.1	A
$I_{CM}$	peak collector current	single pulse; $t_p \leq 1$ ms	-	-	10.2	A
$R_{CEsat}$	collector-emitter saturation resistance	$I_C = 4$ A; $I_B = 200$ mA	[1] -	31	44	m $\Omega$

[1] Pulse test:  $t_p \leq 300$   $\mu$ s;  $\delta \leq 0.02$ .

## 2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Symbol
1	emitter		 sym042
2	collector		
3	base		

## 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBSS303NX	SC-62	plastic surface-mounted package; collector pad for good heat transfer; 3 leads	SOT89

## 4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
PBSS303NX	*5D

- [1] \* = -: made in Hong Kong  
 \* = p: made in Hong Kong  
 \* = t: made in Malaysia  
 \* = W: made in China

## 5. Limiting values

**Table 5. Limiting values**

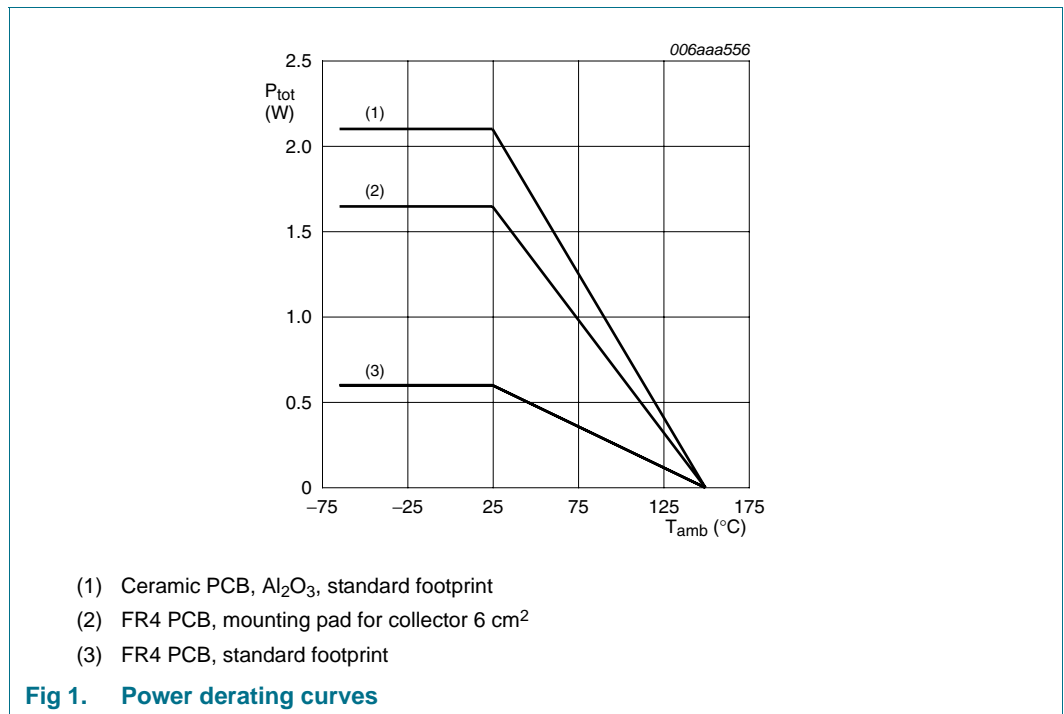
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
$V_{CBO}$	collector-base voltage	open emitter	-	30	V	
$V_{CEO}$	collector-emitter voltage	open base	-	30	V	
$V_{EBO}$	emitter-base voltage	open collector	-	5	V	
$I_C$	collector current		-	5.1	A	
$I_{CM}$	peak collector current	single pulse; $t_p \leq 1$ ms	-	10.2	A	
$P_{tot}$	total power dissipation	$T_{amb} \leq 25$ °C	[1]	-	0.6	W
			[2]	-	1.65	W
			[3]	-	2.1	W
$T_j$	junction temperature		-	150	°C	
$T_{amb}$	ambient temperature		-65	+150	°C	
$T_{stg}$	storage temperature		-65	+150	°C	

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

[3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

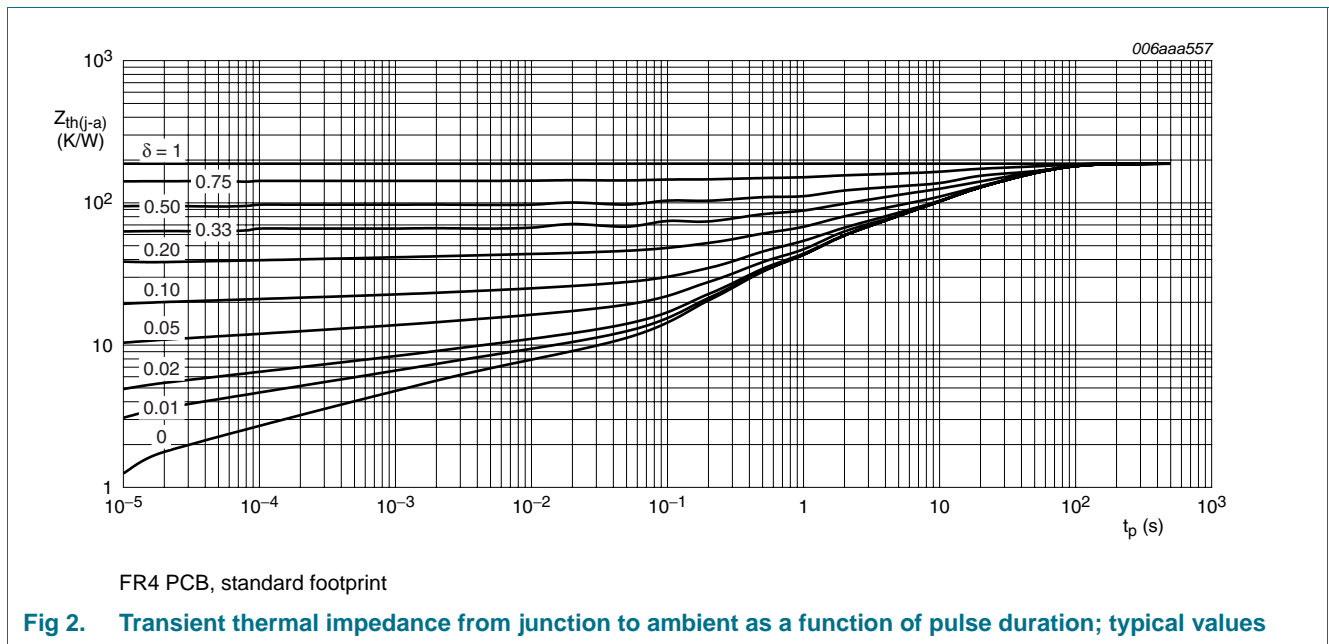


## 6. Thermal characteristics

**Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	208	K/W
			[2]	-	-	76	K/W
			[3]	-	-	60	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	20	K/W	

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.



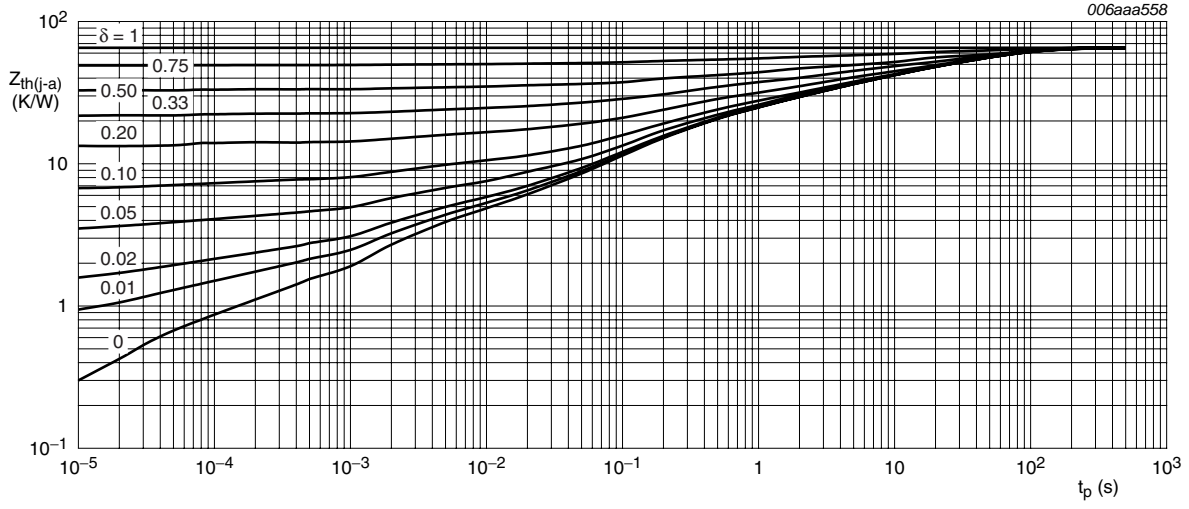


Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

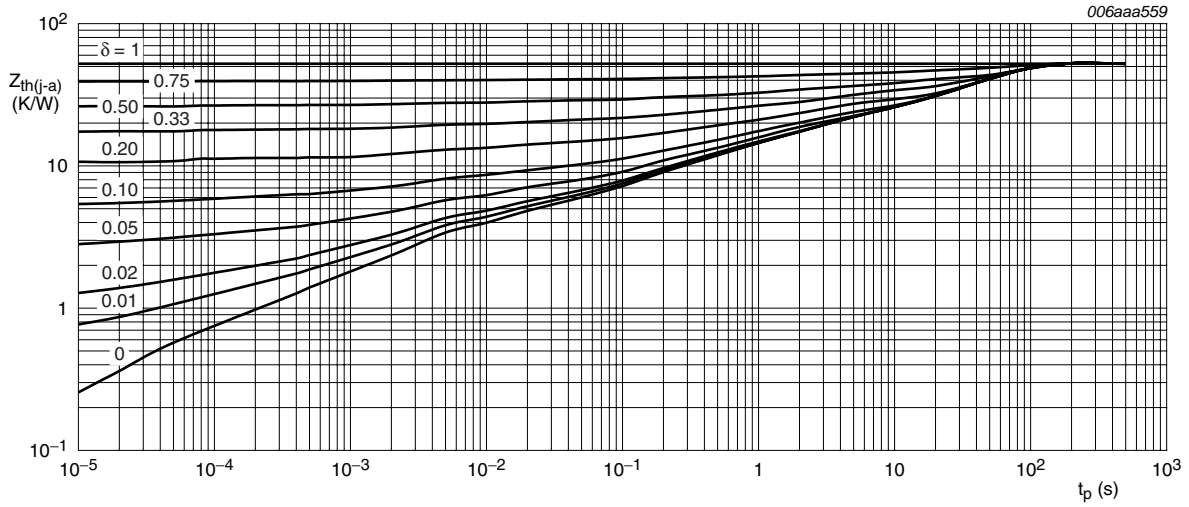


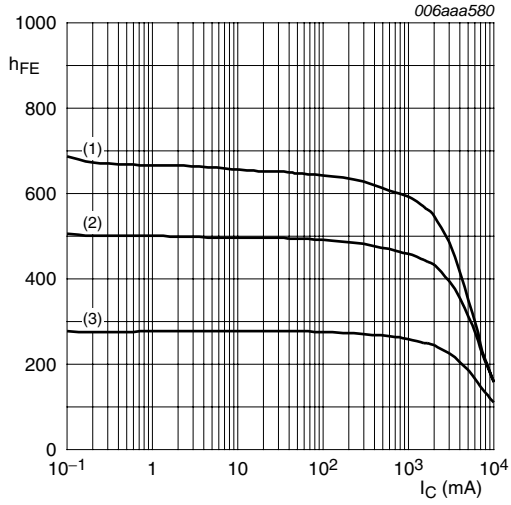
Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 7. Characteristics

**Table 7. Characteristics**
 $T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

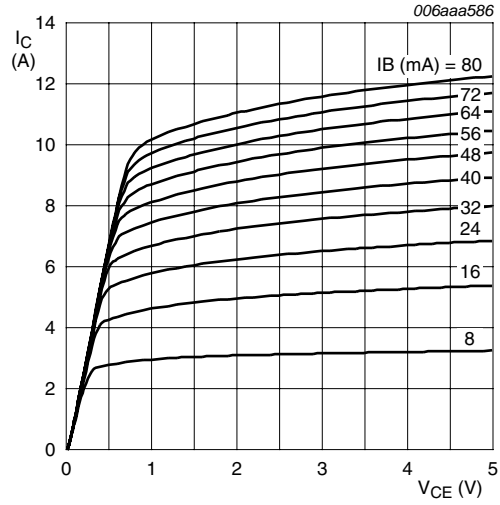
Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
$I_{CBO}$	collector-base cut-off current	$V_{CB} = 30\text{ V}; I_E = 0\text{ A}$	-	-	100	nA	
		$V_{CB} = 30\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ }^{\circ}\text{C}$	-	-	50	$\mu\text{A}$	
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0\text{ A}$	-	-	100	nA	
$h_{FE}$	DC current gain	$V_{CE} = 2\text{ V}; I_C = 0.5\text{ A}$	[1]	300	480	-	
		$V_{CE} = 2\text{ V}; I_C = 1\text{ A}$	[1]	300	460	-	
		$V_{CE} = 2\text{ V}; I_C = 2\text{ A}$	[1]	250	430	-	
		$V_{CE} = 2\text{ V}; I_C = 4\text{ A}$	[1]	200	360	-	
		$V_{CE} = 2\text{ V}; I_C = 6\text{ A}$	[1]	180	270	-	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 0.5\text{ A}; I_B = 50\text{ mA}$	[1]	-	20	30	mV
		$I_C = 1\text{ A}; I_B = 50\text{ mA}$	[1]	-	40	60	mV
		$I_C = 1\text{ A}; I_B = 10\text{ mA}$	[1]	-	60	90	mV
		$I_C = 2\text{ A}; I_B = 40\text{ mA}$	[1]	-	80	110	mV
		$I_C = 4\text{ A}; I_B = 200\text{ mA}$	[1]	-	125	175	mV
		$I_C = 4\text{ A}; I_B = 400\text{ mA}$	[1]	-	120	170	mV
		$I_C = 4\text{ A}; I_B = 40\text{ mA}$	[1]	-	160	250	mV
$R_{CEsat}$	collector-emitter saturation resistance	$I_C = 4\text{ A}; I_B = 200\text{ mA}$	[1]	-	31	44	$\text{m}\Omega$
		$I_C = 4\text{ A}; I_B = 40\text{ mA}$	[1]	-	40	63	$\text{m}\Omega$
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 1\text{ A}; I_B = 100\text{ mA}$	[1]	-	0.81	0.9	V
		$I_C = 4\text{ A}; I_B = 400\text{ mA}$	[1]	-	0.95	1.05	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE} = 2\text{ V}; I_C = 2\text{ A}$	[1]	-	0.75	0.85	V
$t_d$	delay time	$V_{CC} = 12.5\text{ V}; I_C = 3\text{ A}; I_{Bon} = 0.15\text{ A}; I_{Boff} = -0.15\text{ A}$	-	15	-	ns	
$t_r$	rise time		-	50	-	ns	
$t_{on}$	turn-on time		-	65	-	ns	
$t_s$	storage time		-	305	-	ns	
$t_f$	fall time		-	70	-	ns	
$t_{off}$	turn-off time		-	375	-	ns	
$f_T$	transition frequency	$V_{CE} = 10\text{ V}; I_C = 0.1\text{ A}; f = 100\text{ MHz}$	-	130	-	MHz	
$C_c$	collector capacitance	$V_{CB} = 10\text{ V}; I_E = I_e = 0\text{ A}; f = 1\text{ MHz}$	-	60	100	pF	

[1] Pulse test:  $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$ .



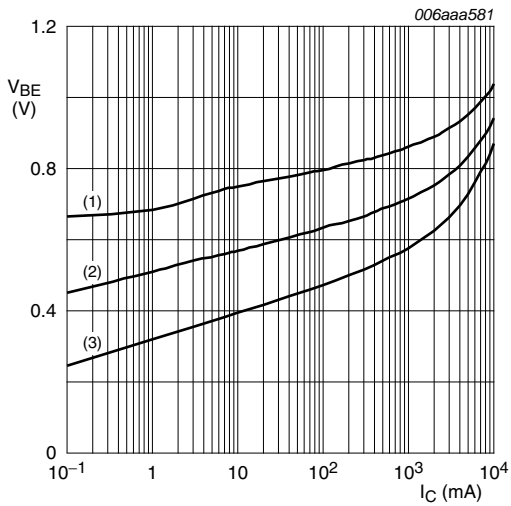
$V_{CE} = 2\text{ V}$   
 (1)  $T_{amb} = 100\text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25\text{ }^\circ\text{C}$   
 (3)  $T_{amb} = -55\text{ }^\circ\text{C}$

**Fig 5. DC current gain as a function of collector current; typical values**



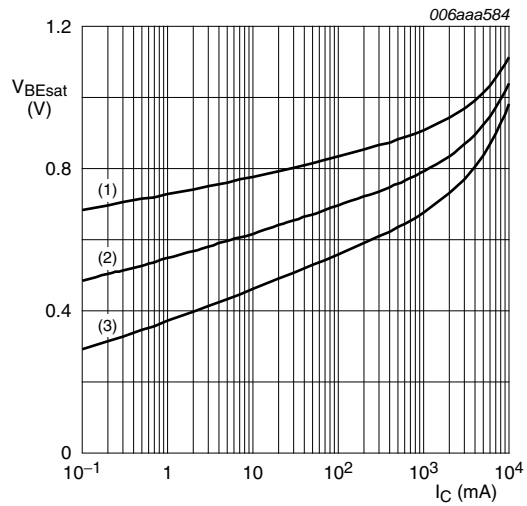
$T_{amb} = 25\text{ }^\circ\text{C}$

**Fig 6. Collector current as a function of collector-emitter voltage; typical values**



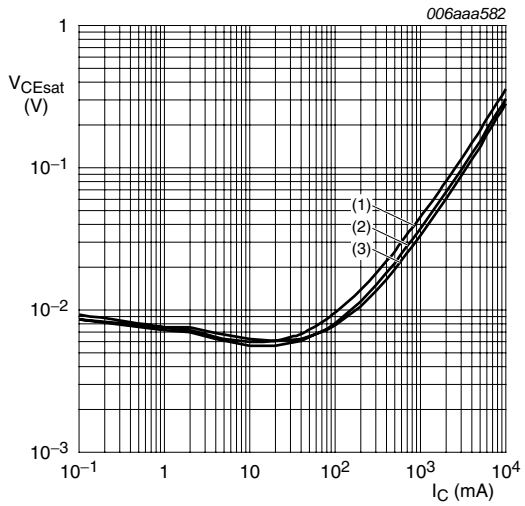
$V_{CE} = 2\text{ V}$   
 (1)  $T_{amb} = -55\text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25\text{ }^\circ\text{C}$   
 (3)  $T_{amb} = 100\text{ }^\circ\text{C}$

**Fig 7. Base-emitter voltage as a function of collector current; typical values**



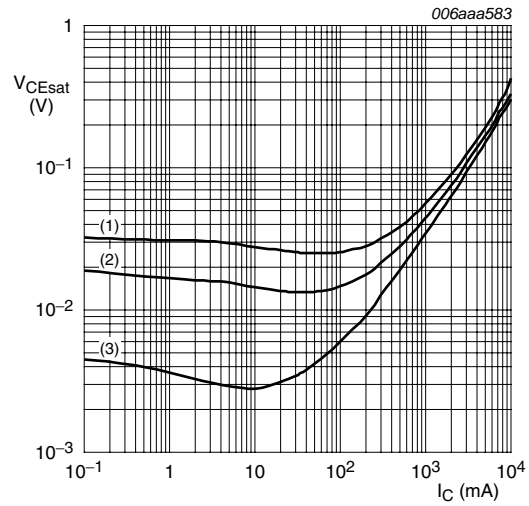
$I_C/I_B = 20$   
 (1)  $T_{amb} = -55\text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25\text{ }^\circ\text{C}$   
 (3)  $T_{amb} = 100\text{ }^\circ\text{C}$

**Fig 8. Base-emitter saturation voltage as a function of collector current; typical values**



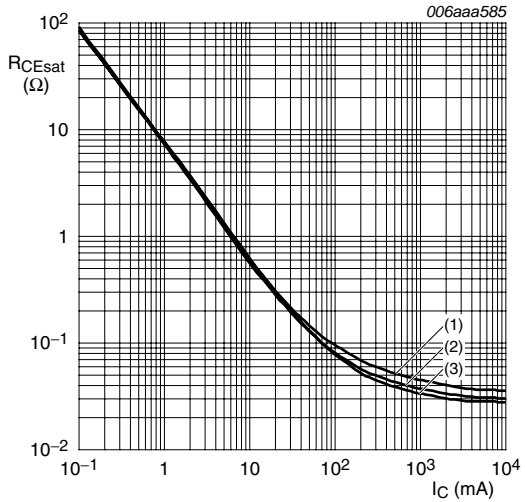
$I_C/I_B = 20$   
 (1)  $T_{amb} = 100\text{ °C}$   
 (2)  $T_{amb} = 25\text{ °C}$   
 (3)  $T_{amb} = -55\text{ °C}$

**Fig 9. Collector-emitter saturation voltage as a function of collector current; typical values**



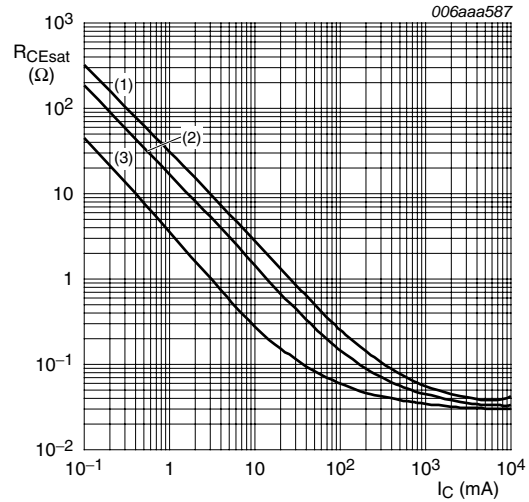
$T_{amb} = 25\text{ °C}$   
 (1)  $I_C/I_B = 100$   
 (2)  $I_C/I_B = 50$   
 (3)  $I_C/I_B = 10$

**Fig 10. Collector-emitter saturation voltage as a function of collector current; typical values**



$I_C/I_B = 20$   
 (1)  $T_{amb} = 100\text{ °C}$   
 (2)  $T_{amb} = 25\text{ °C}$   
 (3)  $T_{amb} = -55\text{ °C}$

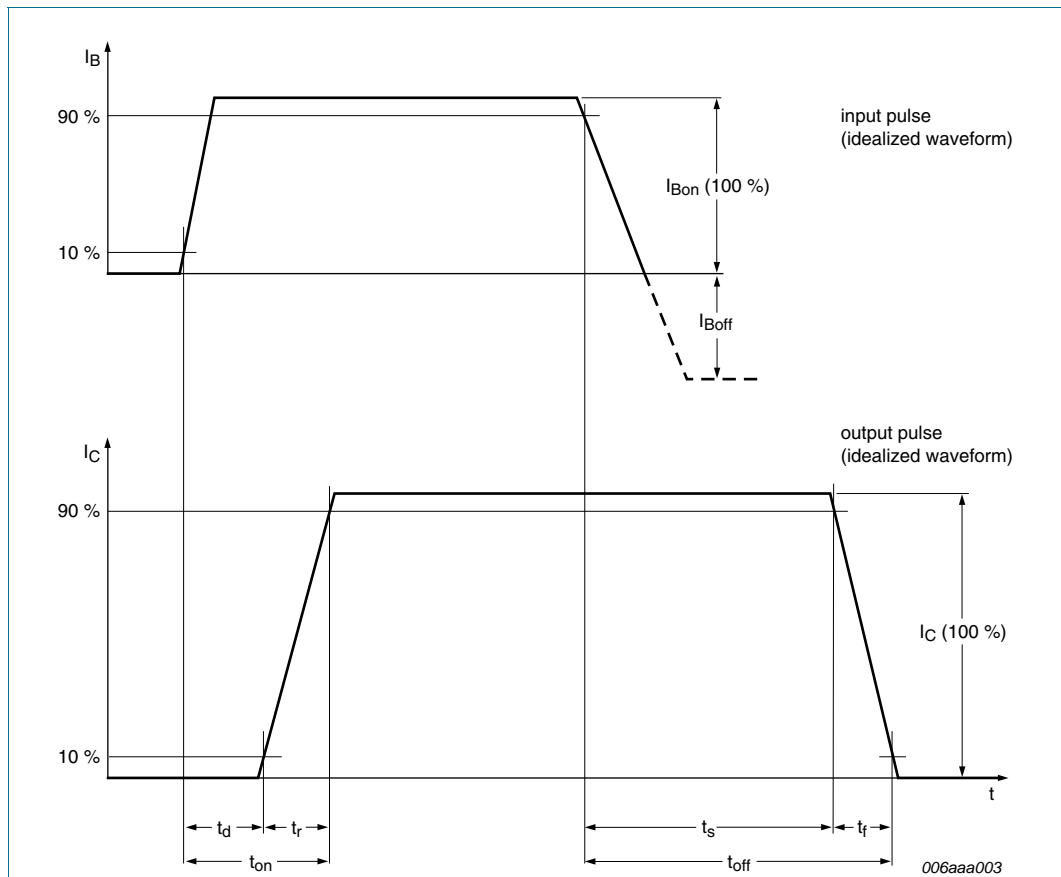
**Fig 11. Collector-emitter saturation resistance as a function of collector current; typical values**



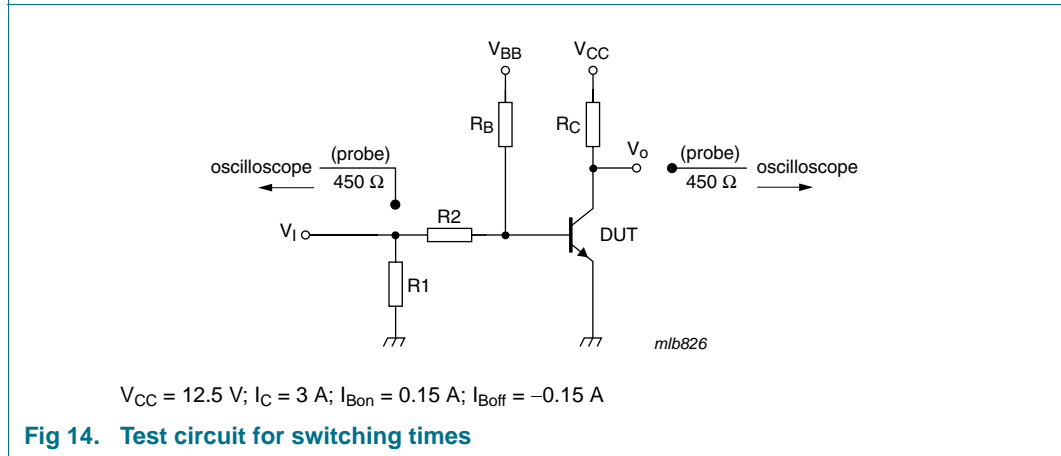
$T_{amb} = 25\text{ °C}$   
 (1)  $I_C/I_B = 100$   
 (2)  $I_C/I_B = 50$   
 (3)  $I_C/I_B = 10$

**Fig 12. Collector-emitter saturation resistance as a function of collector current; typical values**

**8. Test information**



**Fig 13. BISS transistor switching time definition**



**Fig 14. Test circuit for switching times**

## 9. Package outline

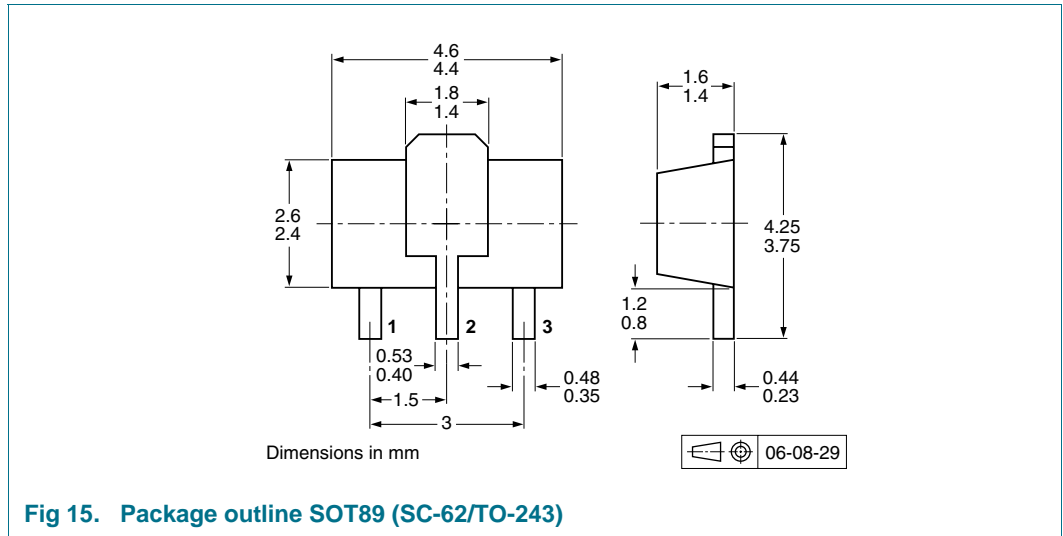


Fig 15. Package outline SOT89 (SC-62/TO-243)

## 10. Packing information

**Table 8. Packing methods**

The indicated -xxx are the last three digits of the 12NC ordering code.<sup>[1]</sup>

Type number	Package	Description	Packing quantity	
			1000	4000
PBSS303NX	SOT89	8 mm pitch, 12 mm tape and reel	-115	-135

[1] For further information and the availability of packing methods, see [Section 15](#).

### 11. Soldering

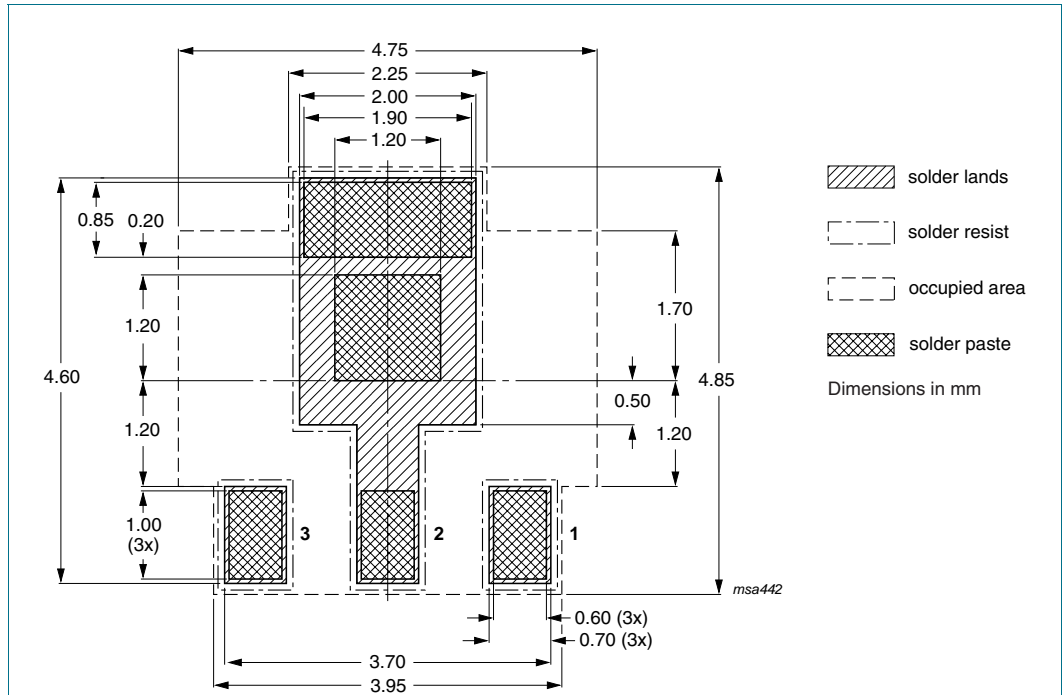
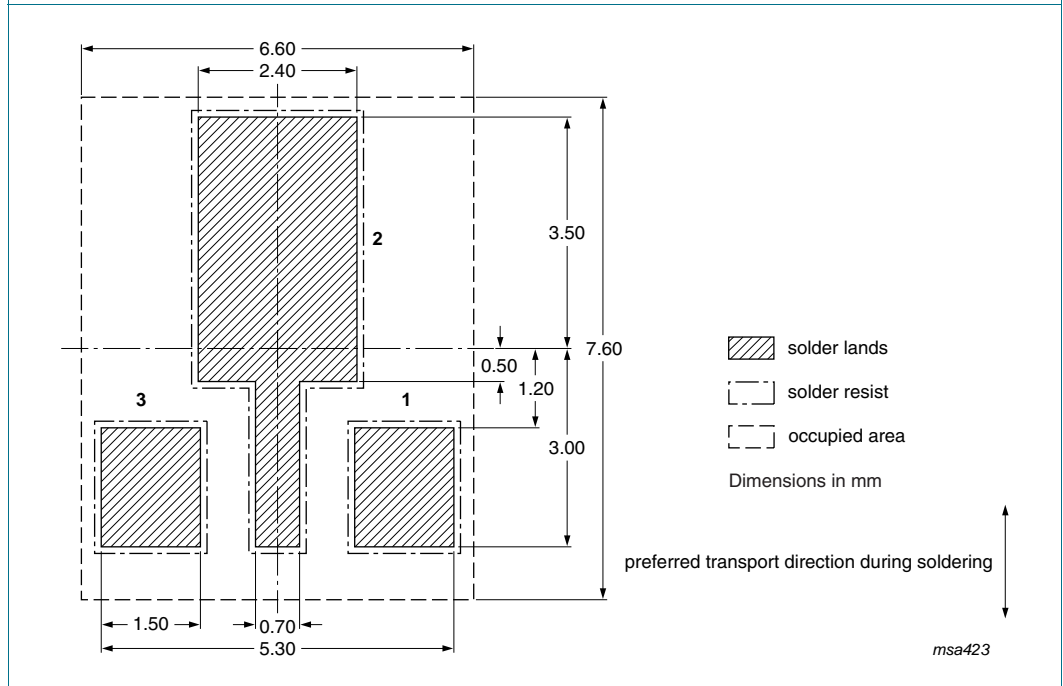


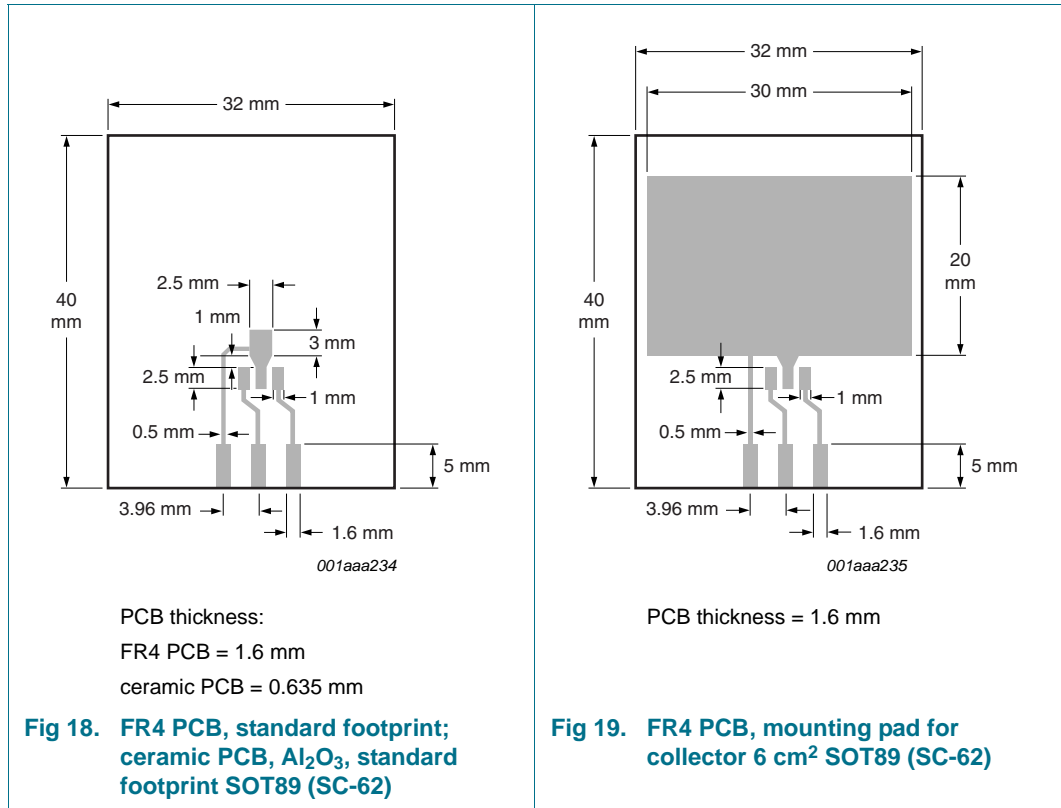
Fig 16. Reflow soldering footprint SOT89 (SC-62)



Not recommended for wave soldering

Fig 17. Wave soldering footprint SOT89 (SC-62)

**12. Mounting**



## 13. Revision history

**Table 9.** Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS303NX_2	20091120	Product data sheet	-	PBSS303NX_1
Modifications:	<ul style="list-style-type: none"> <li>This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content.</li> <li><a href="#">Figure 15 "Package outline SOT89 (SC-62/TO-243)"</a>: updated</li> <li><a href="#">Figure 16 "Reflow soldering footprint SOT89 (SC-62)"</a>: updated</li> <li><a href="#">Figure 17 "Wave soldering footprint SOT89 (SC-62)"</a>: updated</li> </ul>			
PBSS303NX_1	20060823	Product data sheet	-	-

## 14. Legal information

### 14.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Date of release: 20 November 2009

Document identifier: PBSS303NX\_2

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